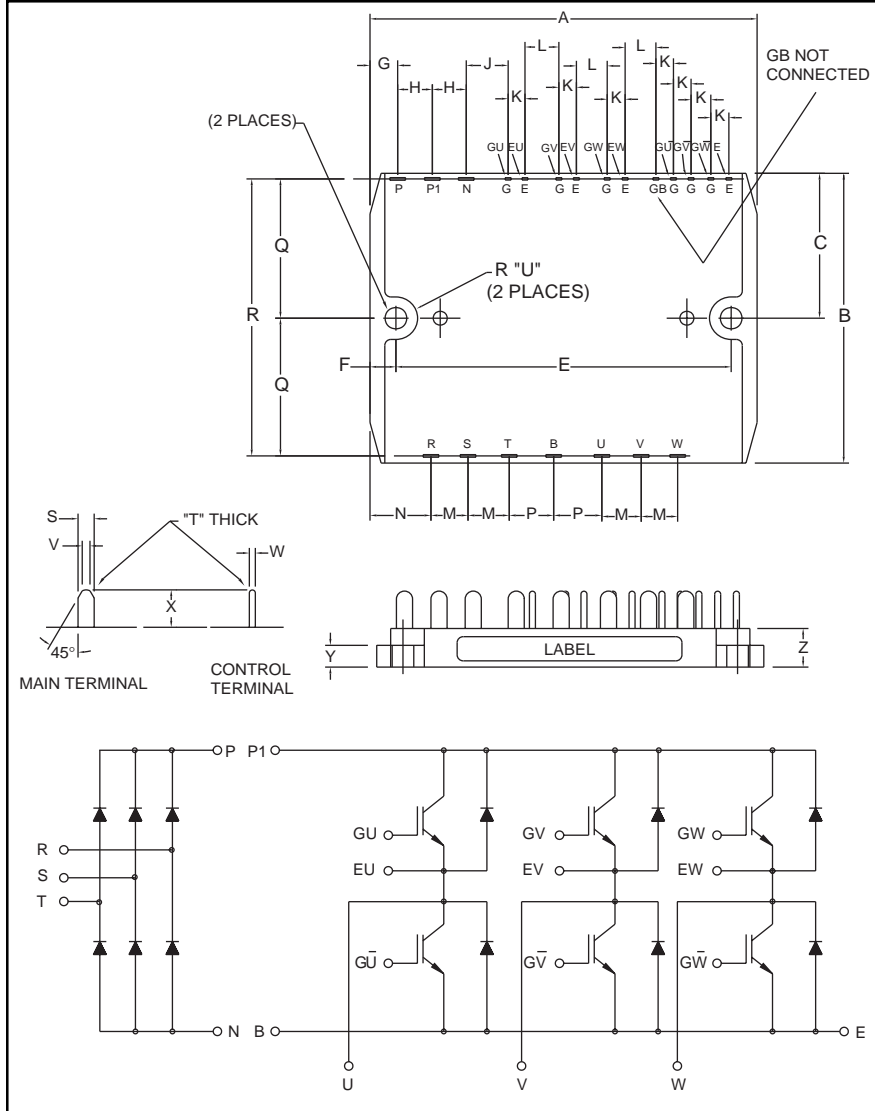


### CI Module

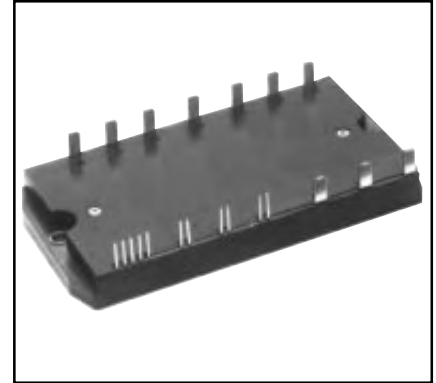
Three Phase Converter +  
Three Phase Inverter  
30 Amperes/600 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.53	115.0
B	2.36	60.0
C	1.18	30.0
D	0.18	4.5
E	4.13	105.0
F	0.20	5.0
G	0.31	8.0
H	0.59	15.0
J	0.68	17.2
K	0.10	2.54
L	0.40	10.16
M	0.49	12.5

Dimensions	Inches	Millimeters
N	0.51	13.0
P	0.59	15.0
Q	1.14	29.0
R	2.28	58.0
S	0.16	4.0
T	0.02	0.6
U	0.22	5.5
V	0.08	2.0
W	0.02	0.6
X	0.35	9.0
Y	0.25	6.3
Z	0.47	12.0



#### Description:

Powerex CI Modules are designed for use in switching applications. Each module consists of a three phase diode converter section and a three phase IGBT inverter section. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

#### Features:

- Low Drive Power
- Low  $V_{CE(sat)}$
- Discrete Super-Fast Recovery (70ns) Free-Wheel Diodes
- High Frequency Operation (20-25 kHz)
- Isolated Baseplate for Easy Heat Sinking

#### Applications:

- AC Motor Control
- Motion/Servo Control
- General Purpose Inverters
- Robotics

#### Ordering Information:

Example: Select the complete nine digit module part number you desire from the table below - i.e. CM30MD1-12H is a 600V ( $V_{CES}$ ), 30 Ampere CI Power Module.

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	30	12



Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (724) 925-7272

**CM30MD1-12H**

**CI Module**

**Three Phase Converter + Three Phase Inverter**

30 Amperes/600 Volts

**Absolute Maximum Ratings,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	CM30MD1-12H	Units
Power Device Junction Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to 125	$^\circ\text{C}$
Mounting Torque, M4 Mounting Screws	—	13	in-lb
Module Weight (Typical)	—	100	Grams
Isolation Voltage, AC 1 minute, 60Hz	$V_{RMS}$	2500	Volts

**Converter Part**

Repetitive Peak Reverse Voltage	$V_{RRM}$	800	Volts
Recommended AC Input Voltage	$E_a$	220	Volts
DC Output Current	$I_O$	30	Amperes
Surge (Non-repetitive) Forward Current	$I_{FSM}$	550	Amperes
$I^2t$ for Fusing	$I^2t$	$1.2 \times 10^3$	$\text{A}^2\text{s}$

**IGBT Inverter Part**

Collector-Emitter Voltage (G-E Short)	$V_{CES}$	600	Volts
Gate-Emitter Voltage (C-E Short)	$V_{GES}$	$\pm 20$	Volts
Collector Current	$I_C$	30	Amperes
Collector Current (Pulse)*	$I_{CM}$	60	Amperes
Emitter Current**	$I_E$	30	Amperes
Emitter Current** (Pulse)*	$I_{EM}$	60	Amperes
Maximum Collector Dissipation	$P_C$	66	Watts

**Electrical and Mechanical Characteristics,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
<b>Converter Sector</b>						
Repetitive Reverse Current	$I_{RRM}$	$V_R = V_{RRM}, T_j = 150^\circ\text{C}$	—	—	8	mA
Forward Voltage Drop	$V_{FM}$	$I_F = 30\text{A}$	—	—	1.5	Volts
Thermal Resistance (Junction-to-Fin)	$R_{th(j-f)}$	Per Diode	—	—	1.7	$^\circ\text{C/W}$
<b>IGBT Inverter Sector</b>						
Collector Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}, V_{GE} = 0\text{V}$	—	—	1	mA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 10\text{V}, I_C = 3.0\text{mA}$	4.5	6.0	7.5	Volts
Gate-Emitter Cutoff Current	$I_{GES}$	$V_{GE} = V_{GES}, V_{CE} = 0\text{V}$	—	—	0.5	$\mu\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{V}, I_C = 30\text{A}, T_j = 25^\circ\text{C}$	—	2.1	2.8	Volts
		$V_{GE} = 15\text{V}, I_C = 30\text{A}, T_j = 150^\circ\text{C}$	—	2.15	—	Volts
Input Capacitance	$C_{ies}$		—	—	3.0	nF
Output Capacitance	$C_{oes}$	$V_{GE} = 0\text{V}, V_{CE} = 10\text{V}$	—	—	2.4	nF
Reverse Transfer Capacitance	$C_{res}$		—	—	0.6	nF
Total Gate Charge	$Q_G$	$V_{CC} = 300\text{V}, I_C = 30\text{A}, V_{GE} = 15\text{V}$	—	90	—	nC
Resistive	Turn-on Delay Time	$V_{GE1} = V_{GE2} = 15\text{V},$ $V_{CC} = 300\text{V}, I_C = 30\text{A},$ $R_g = 21\Omega,$	—	—	120	nS
	Rise Time		—	—	300	nS
Switching	Turn-off Delay Time	Resistive Load	—	—	200	nS
	Fall Time		—	—	300	nS
Emitter-Collector Voltage	$V_{EC}$	$I_E = 30\text{A}, V_{GE} = 0\text{V}$	—	—	2.8	Volts
Reverse Recovery Time	$t_{rr}$	$I_E = 30\text{A}, V_{GE} = 0\text{V},$	—	—	110	nS
Reverse Recovery Charge	$Q_{rr}$	$di_E/dt = -60\text{A}/\mu\text{s}$	—	0.08	—	$\mu\text{C}$
Thermal Resistance (Junction-to-Fin)	$R_{th(j-f)}$	Per IGBT	—	—	1.9	$^\circ\text{C/W}$
		Per FWDi	—	—	2.4	$^\circ\text{C/W}$

\* Pulse width and repetition rate should be such that device junction temperature does not exceed maximum rating.

\*\* Characteristics of the anti-parallel emitter-collector free-wheel diode.